

Schedule by Room (1)

Room	Cap.	Sep. 19 (Tue.)			Sep. 20 (Wed.)			Sep. 21 (Thu.)			Sep. 22 (Fri.)			Sep. 23 (Sat.)		
		AM	PM	AM	PM	AM	PM	AM	PM	AM	PM	AM	PM	AM	PM	
A201	298	09:00 ~ 12:30 12.4 Organic light-emitting devices and organic transistors	14:00 ~ 17:45 T5 The Frontier of China Light-Matter Science	09:30 ~ 12:00 3.14 Silicon photonics and integrated photonics (formerly 3.15)	13:30 ~ 18:00 3.14 Silicon photonics and integrated photonics (formerly 3.15)	09:20 ~ 11:50 NT2 (Open Symposium) Join us! We are looking for you! -Diverse human resources connect the semiconductor industry to the future	13:30 ~ 16:55 T19 Renewed Challenge of Japan to Cutting-Edge Logic Technology	09:00 ~ 12:15 CS.8 Code-sharing Session of 6.1 & 13.3 & 13.5	13:30 ~ 17:15 T13 Novel Physical phenomena and device applications generated by fusion of the magnetism/spin and superconductivity	09:00 ~ 12:00 10.2 Fundamental and exploratory device technologies for spin	09:00 ~ 12:00 10.2 Fundamental and exploratory device technologies for spin	13:30 ~ 16:30 10.2 Fundamental and exploratory device technologies for spin	09:00 ~ 12:00 17.3 Layered materials	13:30 ~ 16:30 17.3 Layered materials		
A202	160	09:00 ~ 11:30 17.3 Layered materials	13:00 ~ 14:45 8.3 Plasma nanotechnology	09:30 ~ 12:00 17.3 Layered materials	13:00 ~ 17:00 T18 Interfacial Nano Electrochemistry: Deepening semiconductor wet processing	09:00 ~ 12:00 17.3 Layered materials	13:30 ~ 17:50 T21 New trend in two-dimensional materials research created by the interaction of light and matter	09:00 ~ 12:00 17.3 Layered materials	13:30 ~ 17:15 T2 Applied Physics for the measure of the Global Warming	09:00 ~ 12:00 17.3 Layered materials	09:00 ~ 12:00 17.3 Layered materials	13:30 ~ 16:30 17.3 Layered materials	09:00 ~ 12:00 17.3 Layered materials	13:30 ~ 16:30 17.3 Layered materials		
A301	240	09:00 ~ 11:45 13.4 Si processing / Si based thin film / MEMS / Equipment technology	14:00 ~ 16:45 T16 Recent progresses of solar cells by oxide semiconductors	09:00 ~ 12:00 13.4 Si processing / Si based thin film / MEMS / Equipment technology	13:00 ~ 18:45 13.6 Nanostructures, quantum phenomena, and nano quantum devices	09:00 ~ 11:35 T12 Frontiers of Quantum Technologies and Trends in Social Implementation	13:00 ~ 15:15 8.2 Plasma deposition of thin film, plasma etching and surface treatment	09:40 ~ 12:00 T7 (Open Symposium) Applied Physics at the Core of Metaverse - Diverse interface technologies connecting people and data -	13:30 ~ 16:20 T7 (Open Symposium) Applied Physics at the Core of Metaverse - Diverse interface technologies connecting people and data -	09:00 ~ 11:30 8.1 Plasma production and diagnostics	09:00 ~ 11:30 8.1 Plasma production and diagnostics	13:00 ~ 16:45 8.1 Plasma production and diagnostics	09:00 ~ 11:30 8.1 Plasma production and diagnostics	13:00 ~ 16:45 8.1 Plasma production and diagnostics		
A302	240	09:00 ~ 11:45 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"	13:00 ~ 17:15 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"	09:00 ~ 11:45 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"	13:00 ~ 17:00 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"	09:00 ~ 12:00 8.2 Plasma deposition of thin film, plasma etching and surface treatment	16:00 ~ 17:00 8.7 Plasma Electronics Invited Talk	09:00 ~ 11:30 FS.1 Focused Session "AI Electronics"	13:00 ~ 17:00 FS.1 Focused Session "AI Electronics"	09:00 ~ 11:30 FS.1 Focused Session "AI Electronics"	09:00 ~ 11:30 FS.1 Focused Session "AI Electronics"	13:00 ~ 16:45 FS.1 Focused Session "AI Electronics"	09:00 ~ 11:30 FS.1 Focused Session "AI Electronics"	13:00 ~ 16:45 FS.1 Focused Session "AI Electronics"		
A303	240	09:00 ~ 11:30 Tutorial (Taro Hitosugi (The Univ. of Tokyo))	14:00 ~ 16:30 Tutorial (Kename Masumoto (Kyutech))	09:00 ~ 11:30 FS.1 Focused Session "AI Electronics"	13:30 ~ 19:00 T17 Accelerating Semiconductor Manufacturing by Cyber-Physical Systems with AI and Optimization Computing	09:00 ~ 12:05 T14 Crossover Symposium "Pioneers and Future Prospects of Molecular Electronics"	13:30 ~ 18:05 T10 Frontiers of Energy Conversion Based on Electron and Ion Transport at Surfaces and Interfaces	09:00 ~ 11:15 13.5 Semiconductor devices/ Interconnect/ Integration technologies	13:30 ~ 17:15 T10 Frontiers of Energy Conversion Based on Electron and Ion Transport at Surfaces and Interfaces	09:00 ~ 12:30 13.3 Insulator technology	09:00 ~ 12:30 13.3 Insulator technology	13:30 ~ 15:30 13.3 Insulator technology	09:00 ~ 12:30 13.3 Insulator technology	13:30 ~ 15:30 13.3 Insulator technology		
A304	240	09:00 ~ 12:00 Semiconductor Seminar(Tadashi Shibata (The Univ. of Tokyo))	13:30 ~ 16:15 T1 Human Resource Development and Education Initiatives in Science Education and Its Revitalization -South Kyushu Region-	09:00 ~ 12:00 13.5 Semiconductor devices/ Interconnect/ Integration technologies	13:00 ~ 17:00 T8 Emerging functionalities of oxides and chalcogenides in iontronics	09:00 ~ 12:00 13.5 Semiconductor devices/ Interconnect/ Integration technologies	13:30 ~ 17:55 T9 Recent Progress of Research Methods in Thin film and Surface Physics	09:00 ~ 11:30 17.1 Carbon nanotubes & other nanocarbon materials	13:00 ~ 14:30 6.4 Thin films and New materials	09:30 ~ 11:45 22.1 Joint Session "Phonon Engineering"	09:30 ~ 11:45 22.1 Joint Session "Phonon Engineering"	13:30 ~ 16:25 T4 Recent advances in photonics and radiation science	09:30 ~ 11:45 22.1 Joint Session "Phonon Engineering"	13:30 ~ 16:25 T4 Recent advances in photonics and radiation science		
A305	71	10:00 ~ 11:30 Award Ceremony	13:00 ~ 17:30 2.1 Detection Devices	09:00 ~ 11:30 3.3 Biomedical optics (formerly 3.4)	13:00 ~ 19:30 3.3 Biomedical optics (formerly 3.4)	09:00 ~ 11:45 2.2 Radiation physics fundamentals & applications, radiation generators, new technology	13:30 ~ 18:25 T6 Korea-Japan Joint Symposium "Photonics Technologies"	09:00 ~ 11:30 17.1 Carbon nanotubes & other nanocarbon materials	13:30 ~ 16:40 T3 Measurement standard to ensure the reliability of radiation measurement	09:00 ~ 12:00 13.8 Optical properties and light-emitting devices	09:00 ~ 12:00 13.8 Optical properties and light-emitting devices	13:30 ~ 17:00 13.8 Optical properties and light-emitting devices	09:00 ~ 12:00 13.8 Optical properties and light-emitting devices	13:30 ~ 17:00 13.8 Optical properties and light-emitting devices		
A306	144	10:00 ~ 11:30 Award Ceremony	13:00 ~ 17:30 2.1 Detection Devices	09:15 ~ 11:30 17.2 Graphene	13:00 ~ 16:15 17.2 Graphene	09:00 ~ 11:30 17.2 Graphene	13:00 ~ 19:15 6.3 Oxide electronics	09:00 ~ 11:30 17.1 Carbon nanotubes & other nanocarbon materials	13:00 ~ 18:45 17.1 Carbon nanotubes & other nanocarbon materials	09:00 ~ 12:00 2.1 Detection Devices	09:00 ~ 12:00 2.1 Detection Devices	13:00 ~ 13:45 2.1 Detection Devices	09:00 ~ 12:00 2.1 Detection Devices	13:00 ~ 15:00 15.2 II-VI and related compounds		
A307	118	09:00 ~ 12:00 2.1 Detection Devices	13:30 ~ 17:30 NT3 (Open Symposium) Transferring your research to the society: from seeds to bloom.	09:30 ~ 12:00 T15 Discussion on basic science and device application of hybrid perovskites	13:30 ~ 16:30 T15 Discussion on basic science and device application of hybrid perovskites	09:00 ~ 11:30 6.3 Oxide electronics	13:00 ~ 19:15 6.3 Oxide electronics	09:30 ~ 11:45 6.6 Probe Microscopy	13:00 ~ 17:30 6.6 Probe Microscopy	09:00 ~ 11:30 6.3 Oxide electronics	09:00 ~ 11:30 6.3 Oxide electronics	13:00 ~ 17:00 6.3 Oxide electronics	09:00 ~ 11:30 6.3 Oxide electronics	13:00 ~ 17:00 6.3 Oxide electronics		
A308	118	09:00 ~ 11:30 2.5 Radiation-induced phosphors	13:30 ~ 16:30 2.5 Radiation-induced phosphors	09:00 ~ 11:30 CS.2 Code-sharing Session of 3.2 & 4.4	13:00 ~ 19:00 CS.2 Code-sharing Session of 3.2 & 4.4	09:15 ~ 12:00 CS.6 Code-sharing Session of 3.10 & 3.14	13:00 ~ 18:00 3.10 Photonic structures and phenomena (formerly 3.11)	09:15 ~ 12:00 6.6 Probe Microscopy	13:15 ~ 18:00 3.10 Photonic structures and phenomena (formerly 3.11)	09:15 ~ 12:00 CS.5 Code-sharing Session of 3.10 & 3.12	09:15 ~ 12:00 CS.5 Code-sharing Session of 3.10 & 3.12	13:00 ~ 16:15 3.13 Optical control devices and optical fibers (formerly 3.14)	09:15 ~ 12:00 CS.5 Code-sharing Session of 3.10 & 3.12	13:00 ~ 16:15 3.13 Optical control devices and optical fibers (formerly 3.14)		
A309	118	09:30 ~ 12:00 9.2 Nanoparticles, Nanowires and Nanosheets	13:30 ~ 16:15 9.2 Nanoparticles, Nanowires and Nanosheets	09:00 ~ 11:30 6.1 Ferroelectric thin films	13:00 ~ 18:15 6.1 Ferroelectric thin films	09:00 ~ 11:30 3.11 Nanoscale optical science and near-field optics (formerly 3.12)	13:00 ~ 18:00 3.11 Nanoscale optical science and near-field optics (formerly 3.12)	09:00 ~ 10:45 4.7 Quantum Optics, Nonlinear Optics and Structured Optics 3.12	13:00 ~ 15:15 3.11 Nanoscale optical science and near-field optics (formerly 3.12)	09:00 ~ 11:00 4.7 Quantum Optics, Nonlinear Optics and Structured Optics	09:00 ~ 11:00 4.7 Quantum Optics, Nonlinear Optics and Structured Optics	13:15 ~ 16:00 CS.4 Code-sharing Session of 3.10 & 3.11	09:00 ~ 11:00 4.7 Quantum Optics, Nonlinear Optics and Structured Optics	13:15 ~ 16:00 CS.4 Code-sharing Session of 3.10 & 3.11		
A310	48	13:00 ~ 17:00 4.2 Photonics Devices, Photonic Integrated Circuit and Silicon Photonics	13:00 ~ 17:00 4.2 Photonics Devices, Photonic Integrated Circuit and Silicon Photonics	09:00 ~ 11:45 CS.1 Code-sharing Session of 2.3 & 7.4	13:30 ~ 16:45 CS.1 Code-sharing Session of 2.3 & 7.4	09:00 ~ 11:30 CS.2 Code-sharing Session of 3.2 & 4.4	13:00 ~ 15:45 9.1 Dielectrics, ferroelectrics and new phenomena	09:00 ~ 10:45 4.7 Quantum Optics, Nonlinear Optics and Structured Optics 3.12	13:00 ~ 15:15 3.11 Nanoscale optical science and near-field optics (formerly 3.12)	09:00 ~ 11:00 4.7 Quantum Optics, Nonlinear Optics and Structured Optics	09:00 ~ 11:00 4.7 Quantum Optics, Nonlinear Optics and Structured Optics	13:00 ~ 14:30 4.7 Quantum Optics, Nonlinear Optics and Structured Optics	09:00 ~ 11:00 4.7 Quantum Optics, Nonlinear Optics and Structured Optics	13:00 ~ 14:30 4.7 Quantum Optics, Nonlinear Optics and Structured Optics		
A311	39	10:30 ~ 11:30 1.2 Education	13:00 ~ 15:30 1.1 Interdisciplinary and General Physics	09:30 ~ 11:45 15.3 III-V-group epitaxial crystals, Fundamentals of epitaxy	13:30 ~ 15:45 15.3 III-V-group epitaxial crystals, Fundamentals of epitaxy	09:30 ~ 11:30 9.5 New functional materials and new phenomena	13:00 ~ 17:00 9.5 New functional materials and new phenomena	09:00 ~ 11:30 9.1 Dielectrics, ferroelectrics	13:00 ~ 15:45 9.1 Dielectrics, ferroelectrics	09:00 ~ 11:30 16.1 Fundamental properties, evaluation, process and devices in disordered materials	09:00 ~ 11:30 16.1 Fundamental properties, evaluation, process and devices in disordered materials	13:30 ~ 15:00 16.2 Energy Harvesting in disordered materials	09:00 ~ 11:30 16.1 Fundamental properties, evaluation, process and devices in disordered materials	13:30 ~ 15:00 16.2 Energy Harvesting in disordered materials		
A401	1738	13:30 ~ 17:30 NT1 (Open Symposium) Restart of Japan's Cutting Edge Logic Semiconductor	13:30 ~ 17:30 NT1 (Open Symposium) Restart of Japan's Cutting Edge Logic Semiconductor	09:45 ~ 10:45 8.8 Plasma Electronics Division Award Speech	13:30 ~ 18:05 T11 The Utilization of Plasma Science for Realizing a Circular Economy	09:30 ~ 12:00 T22 Materials Informatics and Materials Strategies	13:30 ~ 17:15 T22 Materials Informatics and Materials Strategies	09:00 ~ 12:00 8.2 Plasma deposition of thin film, plasma etching and surface treatment	13:30 ~ 17:50 T20 Systematic Building of Green and Sustainable Semiconductor Manufacturing Technologies	09:00 ~ 11:15 12.4 Organic light-emitting devices and organic transistors	09:00 ~ 11:15 12.4 Organic light-emitting devices and organic transistors	13:00 ~ 16:00 3.9 Optical quantum physics and technologies (formerly 3.10)	09:00 ~ 11:15 12.4 Organic light-emitting devices and organic transistors	13:00 ~ 16:00 3.9 Optical quantum physics and technologies (formerly 3.10)		
A501	43	09:00 ~ 11:15 7.3 Micro/Nano patterning and fabrication	13:00 ~ 16:15 7.3 Micro/Nano patterning and fabrication	09:00 ~ 11:15 7.2 Applications and technologies of electron beams	13:00 ~ 16:15 7.2 Applications and technologies of electron beams	09:00 ~ 11:30 9.3 Nanoelectronics	13:00 ~ 14:00 9.3 Nanoelectronics	10:30 ~ 11:15 CS.10 Code-sharing Session of 6.5 & 7.5	13:00 ~ 17:30 6.5 Surface Physics, Vacuum	09:00 ~ 11:30 CS.10 Code-sharing Session of 6.5 & 7.5	09:00 ~ 11:30 CS.10 Code-sharing Session of 6.5 & 7.5	13:00 ~ 17:30 6.5 Surface Physics, Vacuum	09:00 ~ 11:30 CS.10 Code-sharing Session of 6.5 & 7.5	13:00 ~ 17:30 6.5 Surface Physics, Vacuum		
A601	93	09:00 ~ 11:30 7.1 X-ray technologies	13:00 ~ 15:30 7.1 X-ray technologies	09:00 ~ 10:00 3.1 Basic optics and frontier of optics (merged with formerly 3.2 Equipment optics and materials)	13:00 ~ 17:15 3.1 Basic optics and frontier of optics (merged with formerly 3.2 Equipment optics and materials)	09:00 ~ 11:30 3.1 Basic optics and frontier of optics (merged with formerly 3.2 Equipment optics and materials)	13:00 ~ 16:00 3.4 Plasma life sciences	09:00 ~ 11:30 3.9 Optical quantum physics and technologies (formerly 3.10)	13:00 ~ 17:45 CS.9 Code-sharing Session of 6.2 & KS	09:00 ~ 11:30 3.9 Optical quantum physics and technologies (formerly 3.10)	09:00 ~ 11:30 3.9 Optical quantum physics and technologies (formerly 3.10)	13:15 ~ 16:00 3.9 Optical quantum physics and technologies (formerly 3.10)	09:00 ~ 11:30 3.9 Optical quantum physics and technologies (formerly 3.10)	13:15 ~ 16:00 3.9 Optical quantum physics and technologies (formerly 3.10)		
A602	93	09:00 ~ 11:30 4.1 Plasmonics and Nanophotonics	13:00 ~ 18:00 4.1 Plasmonics and Nanophotonics	09:00 ~ 10:00 4.8 Optical Special Lecture	13:00 ~ 18:45 CS.7 Code-sharing Session of 4.5 & 17	09:00 ~ 11:30 3.7 Optical measurement, instrumentation, and sensor (formerly 3.8)	13:00 ~ 16:15 2.4 Medical application	09:00 ~ 11:30 3.7 Optical measurement, instrumentation, and sensor (formerly 3.8)	13:00 ~ 17:45 3.7 Optical measurement, instrumentation, and sensor (formerly 3.8)	09:00 ~ 11:15 15.5 Group IV crystal and alloys	09:00 ~ 11:15 15.5 Group IV crystal and alloys	12:45 ~ 17:00 15.5 Group IV crystal and alloys	09:00 ~ 11:15 15.5 Group IV crystal and alloys	12:45 ~ 17:00 15.5 Group IV crystal and alloys		

Schedule by Room (2)

Room	Cap.	Sep. 19 (Tues.)		Sep. 20 (Wed.)		Sep. 21 (Thu.)		Sep. 22 (Fri.)		Sep. 23 (Sat.)		
		AM	PM	AM	PM	AM	PM	AM	PM	AM	PM	
CVC Auditorium	B101	10:15 ~ 12:00 15.4 III-V-group nitride crystals	13:30 ~ 18:00 15.4 III-V-group nitride crystals	09:00 ~ 12:15 15.4 III-V-group nitride crystals	13:30 ~ 18:00 15.4 III-V-group nitride crystals	09:00 ~ 12:00 15.4 III-V-group nitride crystals	13:30 ~ 18:00 15.4 III-V-group nitride crystals	09:00 ~ 11:45 15.4 III-V-group nitride crystals	13:30 ~ 18:00 15.4 III-V-group nitride crystals	09:00 ~ 12:00 15.4 III-V-group nitride crystals	13:30 ~ 14:45 3.12 Semiconductor optical devices (formerly 3.13)	
	B201	09:00 ~ 11:30 15.7 Crystal characterization, impurities and crystal defects	13:30 ~ 15:15 15.7 Crystal characterization, impurities and crystal defects	10:30 ~ 12:00 15.6 Group IV Compound Semiconductors (SiC)	13:30 ~ 16:00 13.4 Si processing /Si based thin film / MEMS / Equipment technology	09:00 ~ 11:30 8.4 Plasma life sciences	13:30 ~ 17:45 13.7 Compound and power devices, process technology and characterization	09:00 ~ 11:30 13.2 Exploratory Materials, Physical Properties, Devices	13:45 ~ 17:30 13.7 Compound and power devices, process technology and characterization	09:00 ~ 12:00 13.7 Compound and power devices, process technology and characterization	13:30 ~ 14:45 13.7 Compound and power devices, process technology and characterization	
	B202	10:00 ~ 11:45 15.1 Bulk crystal growth	13:30 ~ 15:15 15.1 Bulk crystal growth	09:00 ~ 11:45 CS.11 Code-sharing Session of 8.3 & 9.2	13:30 ~ 18:00 11.1 Fundamental properties	09:45 ~ 11:30 11.1 Fundamental properties	13:30 ~ 16:45 11.1 Fundamental properties	13:30 ~ 17:45 1.6 Ultrasonics	09:00 ~ 11:30 13.2 Exploratory Materials, Physical Properties, Devices	13:30 ~ 17:45 1.6 Ultrasonics	09:30 ~ 12:00 1.5 Instrumentation, measurement and Metrology	13:30 ~ 15:00 1.5 Instrumentation, measurement and Metrology
	B203	09:00 ~ 12:00 3.8 Terahertz technologies (formerly 3.9)	13:30 ~ 18:00 3.8 Terahertz technologies (formerly 3.9)	09:00 ~ 11:45 3.8 Terahertz technologies (formerly 3.9)	13:30 ~ 16:30 3.8 Terahertz technologies (formerly 3.9)	09:00 ~ 12:00 CS.12 Code-sharing Session of 9.4 & M	13:30 ~ 15:15 13.1 Fundamental properties, surface and interface, and simulations of Si related materials	13:30 ~ 14:30 9.4 Thermoelectric conversion	09:00 ~ 12:00 9.4 Thermoelectric conversion	13:30 ~ 14:30 9.4 Thermoelectric conversion	09:00 ~ 12:00 1.4 Energy conversion, storage, resources and environment	13:30 ~ 17:00 1.4 Energy conversion, storage, resources and environment
	B204	09:00 ~ 11:30 3.4 Laser system and materials (formerly 3.5)	13:30 ~ 16:15 3.4 Laser system and materials (formerly 3.5)	09:00 ~ 11:30 3.4 Laser system and materials (formerly 3.5)	13:30 ~ 19:00 11.4 Analog applications and their related technologies	09:00 ~ 11:00 CS.3 Code-sharing Session of 3.4 & 3.13	13:30 ~ 19:00 11.4 Analog applications and their related technologies	13:30 ~ 17:30 3.5 Ultrashort-pulse and high-intensity lasers (formerly 3.6)	09:30 ~ 11:15 3.5 Ultrashort-pulse and high-intensity lasers (formerly 3.6)	13:30 ~ 17:30 3.5 Ultrashort-pulse and high-intensity lasers (formerly 3.6)	09:00 ~ 12:00 3.5 Ultrashort-pulse and high-intensity lasers (formerly 3.6)	13:30 ~ 17:00 3.5 Ultrashort-pulse and high-intensity lasers (formerly 3.6)
	B205	13:30 ~ 18:30 4.3 Lasers and laser materials processing	13:30 ~ 18:30 4.3 Lasers and laser materials processing	09:00 ~ 11:30 3.6 Laser processing (formerly 3.7)	13:30 ~ 17:30 3.6 Laser processing (formerly 3.7)	09:00 ~ 11:45 3.6 Laser processing (formerly 3.7)	13:30 ~ 15:45 3.6 Laser processing (formerly 3.7)	13:30 ~ 19:00 12.1 Fabrications and Structure Controls	09:00 ~ 12:00 12.1 Fabrications and Structure Controls	13:30 ~ 19:00 12.1 Fabrications and Structure Controls	09:00 ~ 12:00 13.2 Exploratory Materials, Physical Properties, Devices	13:30 ~ 14:45 13.2 Exploratory Materials, Physical Properties, Devices
	C301	09:00 ~ 16:45 11.2 Thin and thick superconducting films, coated conductors and film crystal growth	13:45 ~ 14:45 1.3 Novel technologies and interdisciplinary engineering	09:00 ~ 10:45 11.3 Critical Current, Superconducting Power Applications	13:30 ~ 17:15 11.5 Junction and circuit fabrication process, digital applications	13:30 ~ 16:45 11.2 Thin and thick superconducting films, coated conductors and film crystal growth	13:30 ~ 17:15 11.5 Junction and circuit fabrication process, digital applications	13:30 ~ 16:15 16.1 Fundamental properties, evaluation, process and devices in disordered materials	10:00 ~ 11:00 4.6 Terahertz Photonics	13:30 ~ 16:15 16.1 Fundamental properties, evaluation, process and devices in disordered materials	09:00 ~ 11:30 16.1 Fundamental properties, evaluation, process and devices in disordered materials	13:30 ~ 16:15 16.1 Fundamental properties, evaluation, process and devices in disordered materials
	C401	09:00 ~ 12:30 1.3 Novel technologies and interdisciplinary engineering	13:45 ~ 14:45 1.3 Novel technologies and interdisciplinary engineering	09:00 ~ 12:30 1.3 Novel technologies and interdisciplinary engineering	13:45 ~ 14:45 1.3 Novel technologies and interdisciplinary engineering	09:00 ~ 10:45 CS.9 Code-sharing Session of 6.2 & KS	13:30 ~ 18:00 6.2 Carbon-based thin films	13:30 ~ 18:00 6.2 Carbon-based thin films	09:00 ~ 11:30 3.12 Semiconductor optical devices (formerly 3.13)	13:30 ~ 18:00 6.2 Carbon-based thin films	09:00 ~ 11:45 3.12 Semiconductor optical devices (formerly 3.13)	09:00 ~ 11:45 3.12 Semiconductor optical devices (formerly 3.13)
	C402	09:00 ~ 12:00 10.1 Emerging materials in spintronics and magnetics (including fabrication and characterization methodologies)	13:30 ~ 17:30 10.4 Spintronics in semiconductor, topological material, superconductor, and multiferroics	09:00 ~ 12:00 10.1 Emerging materials in spintronics and magnetics (including fabrication and characterization methodologies)	13:30 ~ 17:30 10.4 Spintronics in semiconductor, topological material, superconductor, and multiferroics	09:00 ~ 10:30 10.1 Emerging materials in spintronics and magnetics (including fabrication and characterization methodologies)	13:30 ~ 18:00 10.3 Spin devices, magnetic memories and storages	13:30 ~ 18:45 10.3 Spin devices, magnetic memories and storages	09:30 ~ 11:45 22.1 Joint Session M "Phonon Engineering"	13:30 ~ 17:00 22.1 Joint Session M "Phonon Engineering"	09:30 ~ 11:45 22.1 Joint Session M "Phonon Engineering"	13:30 ~ 17:00 22.1 Joint Session M "Phonon Engineering"
	TKP Kumamoto	C601	13:30 ~ 17:45 23.1 Joint Session N "Informatics"	13:30 ~ 18:00 23.1 Joint Session N "Informatics"	09:00 ~ 11:45 13.9 Compound solar cells	13:30 ~ 18:00 23.1 Joint Session N "Informatics"	13:30 ~ 20:00 12.5 Organic and hybrid solar cells	13:30 ~ 19:45 12.5 Organic and hybrid solar cells	09:00 ~ 12:00 12.5 Organic and hybrid solar cells	13:30 ~ 19:45 12.5 Organic and hybrid solar cells	09:00 ~ 12:00 12.5 Organic and hybrid solar cells	13:30 ~ 17:45 12.5 Organic and hybrid solar cells
D901		09:00 ~ 12:00 12.3 Functional Materials and Novel Devices	13:30 ~ 17:45 12.3 Functional Materials and Novel Devices	09:00 ~ 12:00 CS.14 Code-sharing Session of 12.6 & 12.7	13:30 ~ 17:45 12.3 Functional Materials and Novel Devices	09:00 ~ 11:45 12.6 Nanobiotechnology	13:30 ~ 19:00 12.6 Nanobiotechnology	09:00 ~ 11:45 12.6 Nanobiotechnology	13:30 ~ 17:00 12.3 Functional Materials and Novel Devices	09:00 ~ 11:45 12.6 Nanobiotechnology	13:30 ~ 17:00 12.3 Functional Materials and Novel Devices	
D902		09:00 ~ 12:00 12.3 Functional Materials and Novel Devices	13:30 ~ 18:00 12.2 Characterization and Materials Physics	09:00 ~ 12:00 12.3 Functional Materials and Novel Devices	13:30 ~ 18:15 12.2 Characterization and Materials Physics	09:00 ~ 11:45 CS.13 Code-sharing Session of 12.5 & 13.9 & 16.3	13:30 ~ 18:15 12.2 Characterization and Materials Physics	13:30 ~ 18:30 12.4 Organic light-emitting devices and organic transistors	09:00 ~ 12:00 12.4 Organic light-emitting devices and organic transistors	13:30 ~ 16:30 12.4 Organic light-emitting devices and organic transistors	09:00 ~ 12:30 12.4 Organic light-emitting devices and organic transistors	

Schedule by Room (3)

Room	Cap.	Sep. 19 (Tue.)	Sep. 20 (Wed.)	Sep. 21 (Thu.)	Sep. 22 (Fri.)
		AM	AM	PM	PM
Exhibition Hall, 1F Kumamoto Jo Hall	P01 ~ P23				
		<p>[13:30-15:30]</p> <p>17 Nanocarbon and Two-Dimensional Materials</p>	<p>[13:30-15:30]</p> <p>2 Ionizing Radiation</p> <p>9.1 Dielectrics, ferroelectrics and Nanosheets</p> <p>9.2 Nanoparticles, Nanowires and Nanosheets</p> <p>9.3 Nanoelectronics</p> <p>9.5 New functional materials and new phenomena</p> <p>13.9 Compound solar cells</p>	<p>[13:30-15:30]</p> <p>8.1 Plasma production and diagnostics</p> <p>8.3 Plasma nanotechnology</p> <p>8.5 Plasma phenomena, emerging area of plasmas and their new applications</p> <p>15.1 Bulk crystal growth</p> <p>15.3 III-V-group epitaxial crystals, Fundamentals of epitaxy</p> <p>15.4 III-V-group nitride crystals</p> <p>15.7 Crystal characterization, impurities and crystal defects</p> <p>16.1 Fundamental properties, evaluation, process and devices in disordered materials</p> <p>21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"</p>	<p>[13:30-15:30]</p> <p>8.1 Plasma production and diagnostics</p> <p>8.3 Plasma nanotechnology</p> <p>8.5 Plasma phenomena, emerging area of plasmas and their new applications</p> <p>15.1 Bulk crystal growth</p> <p>15.3 III-V-group epitaxial crystals, Fundamentals of epitaxy</p> <p>15.4 III-V-group nitride crystals</p> <p>15.7 Crystal characterization, impurities and crystal defects</p> <p>16.1 Fundamental properties, evaluation, process and devices in disordered materials</p> <p>21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"</p>
		<p>[09:30-11:30]</p> <p>6.2 Carbon-based thin films</p> <p>6.3 Oxide electronics</p> <p>11 Superconductivity</p> <p>23.1 Joint Session N "Informatics"</p>	<p>[09:30-11:30]</p> <p>4 JSAP-Optica Joint Symposia 2023</p> <p>6.1 Ferroelectric thin films</p> <p>6.4 Thin films and New materials</p> <p>6.5 Surface Physics, Vacuum</p> <p>6.6 Probe Microscopy</p> <p>13.7 Compound and power devices, process technology and characterization</p> <p>15.6 Group IV Compound Semiconductors (SiC)</p> <p>22.1 Joint Session M "Phonon Engineering"</p>	<p>[16:00-18:00]</p> <p>3.1 Basic optics and frontier of optics (merged with formerly 3.2 Equipment optics and materials)</p> <p>3.2 Information photonics and image engineering (formerly 3.3)</p> <p>3.3 Biomedical optics (formerly 3.4)</p> <p>3.4 Laser system and materials (formerly 3.5)</p> <p>3.5 Ultrashort-pulse and high-intensity lasers (formerly 3.6)</p> <p>3.6 Laser processing (formerly 3.7)</p> <p>3.7 Optical measurement, instrumentation, and sensor (formerly 3.8)</p> <p>3.8 Terahertz technologies (formerly 3.9)</p> <p>3.9 Optical quantum physics and technologies (formerly 3.10)</p> <p>3.10 Photonic structures and phenomena (formerly 3.11)</p> <p>3.12 Semiconductor optical devices (formerly 3.13)</p> <p>3.13 Optical control devices and optical fibers (formerly 3.14)</p> <p>3.14 Silicon photonics and integrated photonics (formerly 3.15)</p> <p>9.4 Thermoelectric conversion</p>	<p>[16:00-18:00]</p> <p>3.11 Nanoscale optical science and near-field optics (formerly 3.12)</p> <p>13.1 Fundamental properties, surface and interface, and simulations of Si related materials</p> <p>13.2 Exploratory Materials, Physical Properties, Devices</p> <p>13.3 Insulator technology</p> <p>13.4 Si processing /Si based thin film / MEMS / Equipment technology</p> <p>13.6 Nanostructures, quantum phenomena, and nano quantum devices</p> <p>13.8 Optical properties and light-emitting devices</p>